

FIG. 1

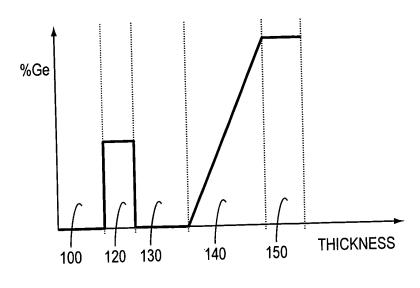


FIG. 2

Title: Semiconductor Heterostructures and Related

Methods

Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent MLBeloborodov/BRChase

Formal Drawings

	QUALITATIVE EVALUATION OF DISLOCATION PILE-UP DENSITY			
% Ge	H* = 0.6 T _{crit}	H = 1.25 T _{crit}	H = 2 T _{crit}	H = 5 T _{crit}
5	HIGH	MEDIUM	LOW	LOW
10	HIGH	MEDIUM	MEDIUM	LOW
15	HIGH	MEDIUM	MEDIUM	LOW

^{*} THICKNESS (H) OF THE SEED LAYER RELATIVE TO ITS CRITICAL THICKNESS (T_{crit}).

FIG. 3

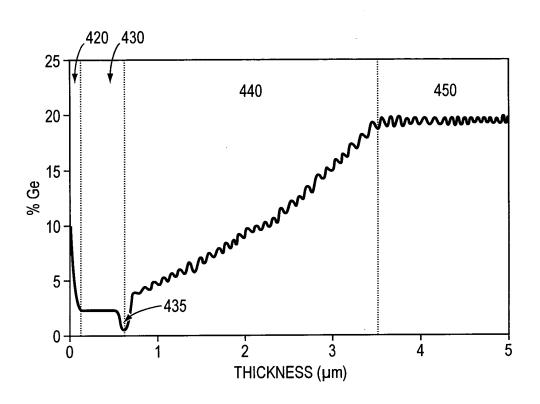


FIG. 4

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Formal Drawings

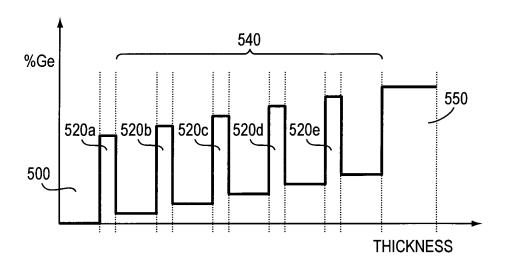


FIG. 5

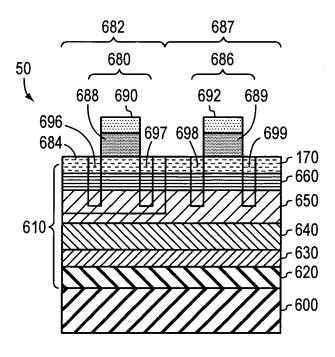


FIG. 6